

BD912

Rev. H Oct.-2018

TO-220

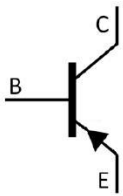
PNP

Silicon PNP transistor in a TO-220 Plastic Package.

, BD911

High V_{CEO} , high I_C , complement to BD911.

Use in power linear and switching applications.



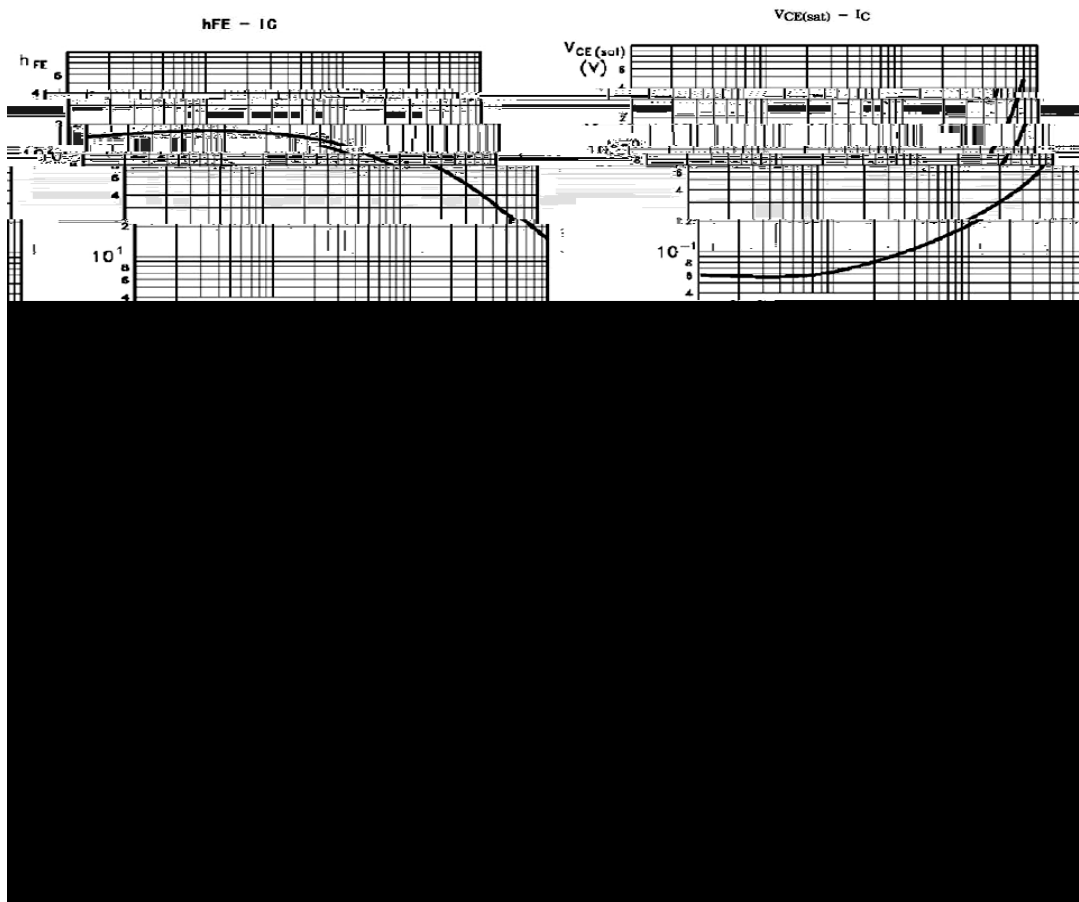
PIN 1 Base PIN 2 Collector PIN 3 Emitter

BD912

Rev. H Oct.-2018

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-15	A
Base Current – Continuous	I_B	-5.0	A
Collector Power Dissipation	$P_C(T_C=25^\circ\text{C})$	90	W
Junction Temperature	T_j	150 T	

/ Electrical Characteristic Curve

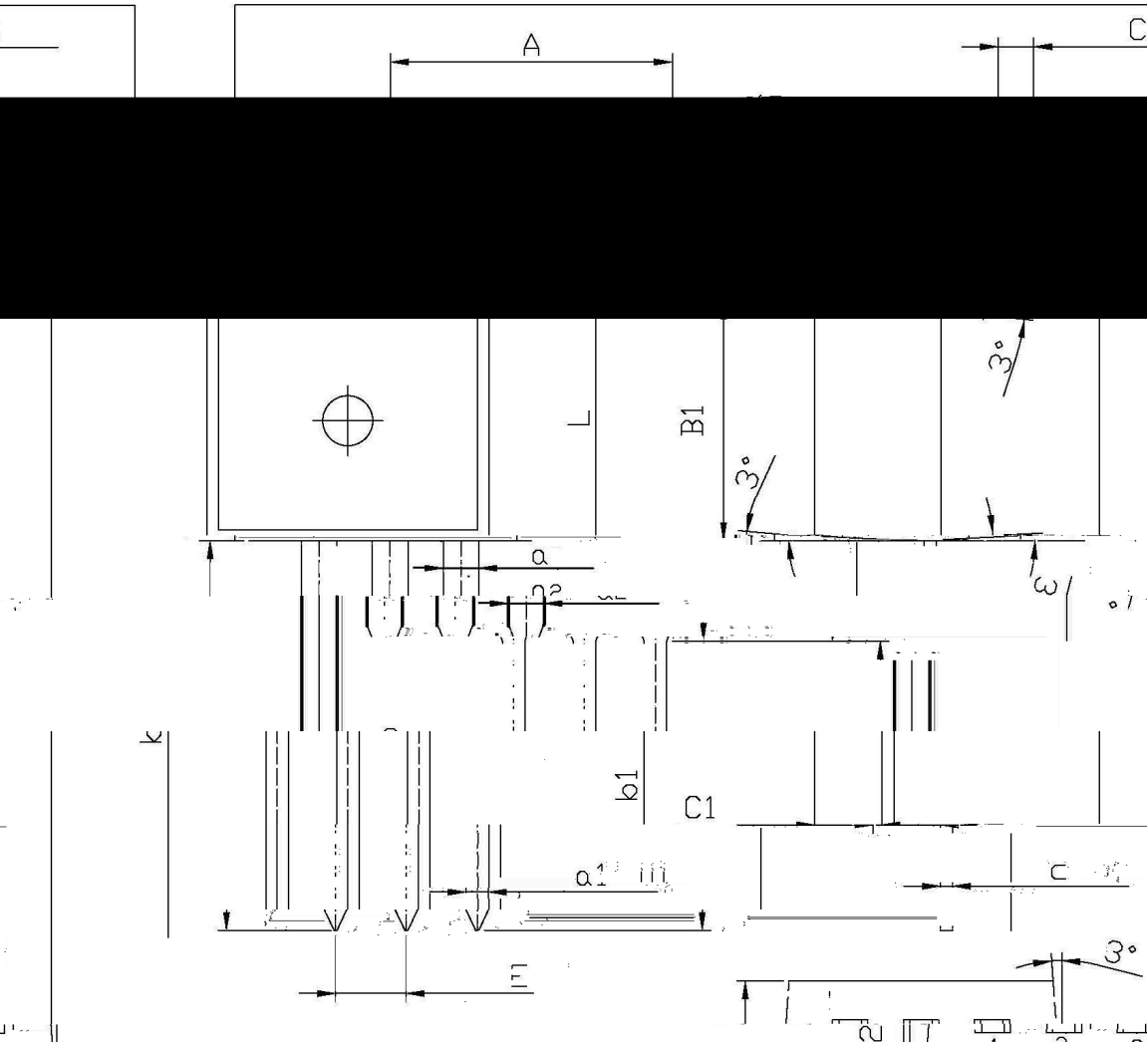


/ Package Dimensions

mm

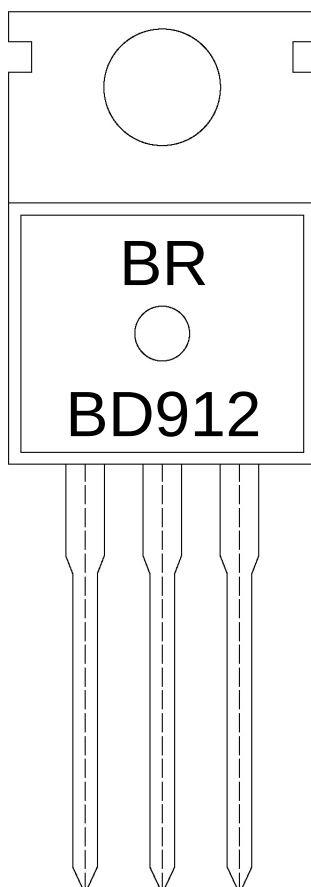
TO-220

单位:



Dimensions in Millimeters			Dimensions in Millimeters		
Symbol	Min	Max	Symbol	Min	Max
A	9.8	10.2	C	1.2	1.4
B	3.56	3.64	B1	6.3	6.7
a	9.0	9.4	F	15.7	16.1
a1	9.6	10.0	h1	12.5	13.0
c	1.22	1.32	a	0.4	0.6
c1	0.2	0.25			
		1.45			

/ Marking Instructions



BR

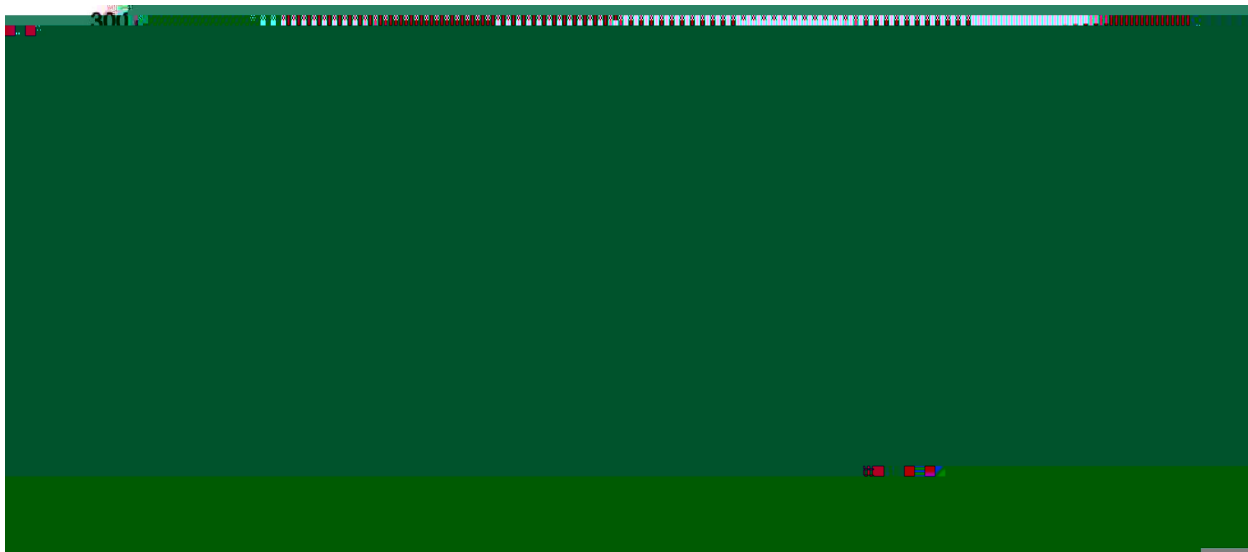
BD912

Note:

BR: Company Code

BD912: Product Type.

****: Lot No. Code, code change with Lot No.


() / Temperature Profile for Dip Soldering(Pb-Free)


Note:

- 1 25 150 60 90sec;
 2 255±5 5±0.5sec;
 3 2 10 /sec.

- 1.Preheating:25~150 , Time:60~90sec.
 2.Peak Temp.:255±5 , Duration:5±0.5sec.
 3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5

10±1 sec.

Temp.:270±5

Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 袋	袋 盒	只 盒	盒 箱	只 箱	袋	盒	箱